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SHEET 1 OF 1 ATTY. DOCKET NO. SERIAL NO. 10/663,714 57810-076 **APPLICANT** Daijiro INOUE, et al. GROUP FILING DATE September 17, 2003 U.S. PATENT DOCUMENTS **Publication Date** Name of Patentee or Applicant of Cited Pages, Columns, Lines, Where Relevant Document Passages or Relevant Figures Appear FOREIGN PATENT DOCUMENTS Translation Publication Date Name of Patentee or Applicant Pages, Columns. of Cited Document Lines Where Relevant **Figures** Appear No Yes JAPAN (w/English TOSHIBA CORP. Abstract) SANYO ELECTRIC CO LTD JAPAN (w/English Abstract) JAPAN (w/English MATSUSHITA ELECTRIC IND COLTD Abstract) NICHIA CHEM IND LTD JAPAN (w/English Abstract) **FUJITSU LTD** JAPAN (w/English Abstract) TOSHIBA CORP. JAPAN (w/English

JP 2002-299768 10/11/2002 JP 2001-57461 02/27/2001 JP 11-340580 12/10/1999 JP 10-294529 11/4/1998 Abstract) OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.) **EXAMINER'S** Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, INITIALS serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. **C**ITE T. Asano, et al. " High-power 400-nm-band AlGainN-based laser diodes with low aspect ratio." Applied Physics Letters, Volume 80. Number 19, May 13, 2002, pp.3497-3499 Nishinaga Tatau, " Hetero-epitaxy with Large Lattice Mismatch and Microchannel Epitaxy of Compound Semiconductor."

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